DA121TT1G

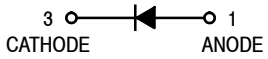
Silicon Switching Diode

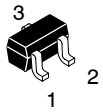
Features

- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

http://onsemi.com





SOT−416 / SC−75
CASE 463
STYLE 2

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Continuous Reverse Voltage	V_R	80	V
Recurrent Peak Forward Current	I_F	200	mA
Peak Forward Surge Current Pulse Width = 10 μs	$I_{FM(surge)}$	500	mA

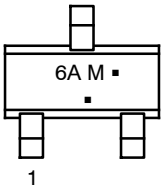
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, FR−4 Board (Note 1) T_A = 25°C Derated above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	555	°C/W
Total Device Dissipation, FR−4 Board (Note 2) T_A = 25°C Derated above 25°C	P_D	360 2.9	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	345	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR−4 @ Minimum Pad
2. FR−4 @ 1.0 × 1.0 Inch Pad

MARKING DIAGRAM



6A = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
DA121TT1G	SOT−416 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Forward Voltage –	V_F			mV
(I_F = 1.0 mA)		–	715	
(I_F = 10 mA)		–	866	
(I_F = 50 mA)		–	1000	
(I_F = 150 mA)		–	1250	
Reverse Current –	I_R			μA
(V_R = 75 V)		–	1.0	
(V_R = 75 V, T_J = 150°C)		–	50	
(V_R = 25 V, T_J = 150°C)		–	30	
Capacitance – (V_R = 0, f = 1.0 MHz)	C_D	–	2.0	pF
Reverse Recovery Time – (I_F = I_R = 10 mA, R_L = 50 Ω) (Figure 1)	t_{rr}	–	6.0	ns
Stored Charge – (I_F = 10 mA to V_R = 6.0 V, R_L = 500 Ω) (Figure 2)	QS	–	45	PC
Forward Recovery Voltage – (I_F = 10 mA, t_r = 20 ns) (Figure 3)	V_{FR}	–	1.75	V

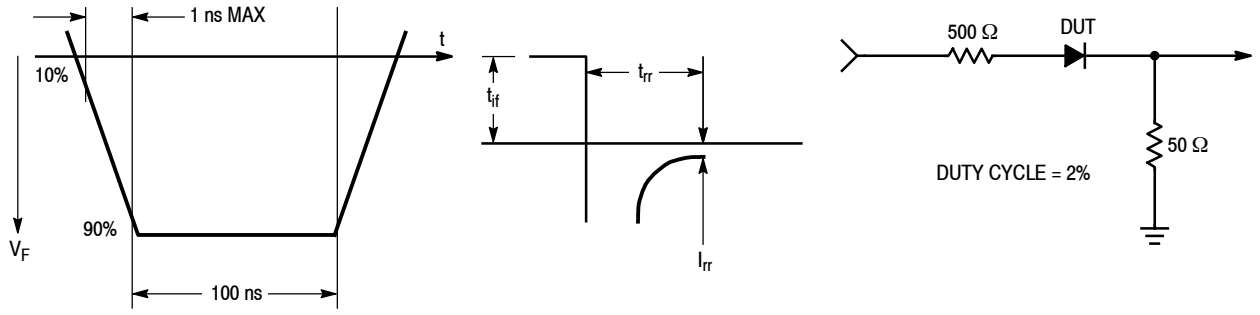


Figure 1. Reverse Recovery Time Equivalent Test Circuit

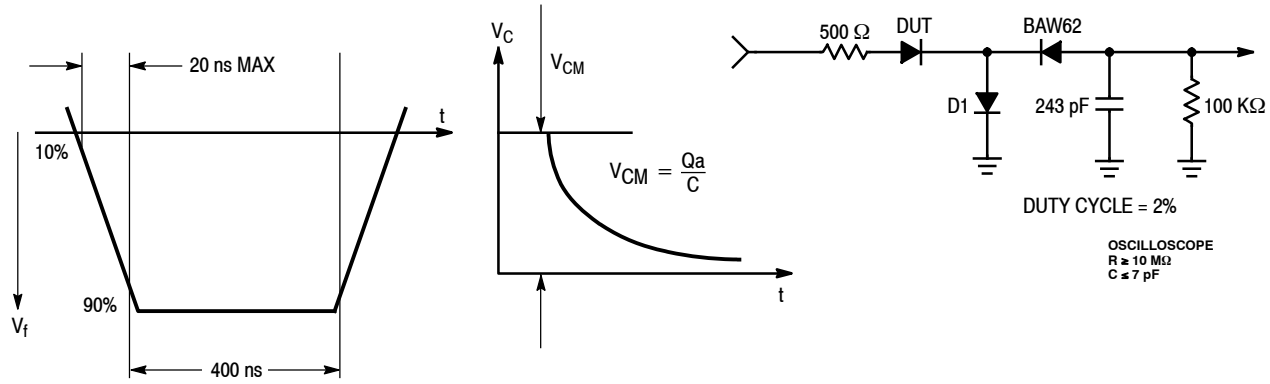


Figure 2. Recovery Charge Equivalent Test Circuit

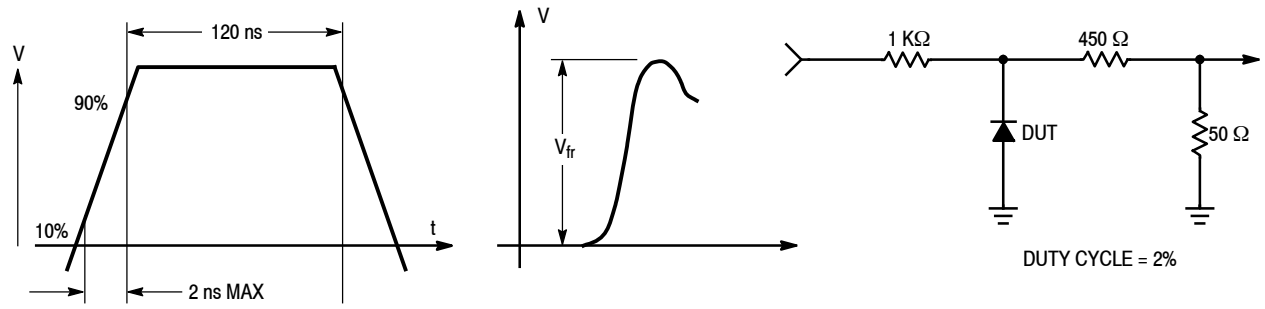


Figure 3. Forward Recovery Voltage Equivalent Test Circuit

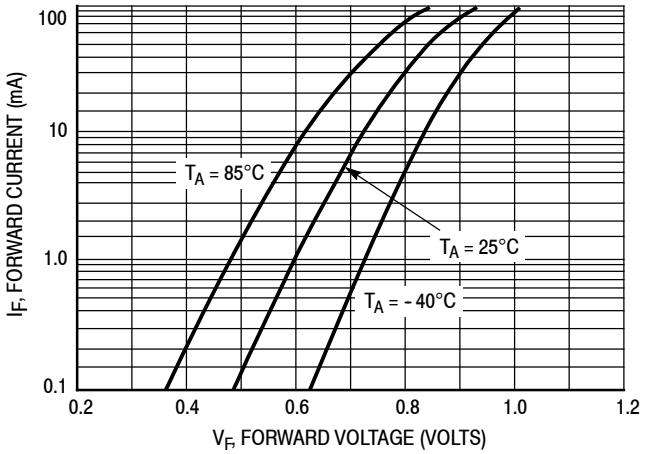


Figure 4. Forward Voltage

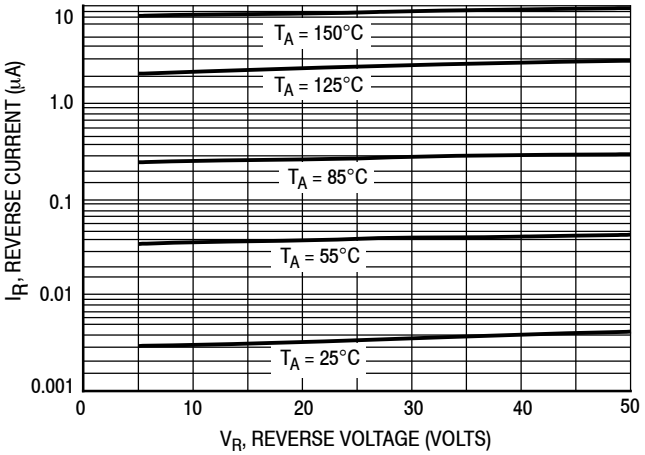


Figure 5. Leakage Current

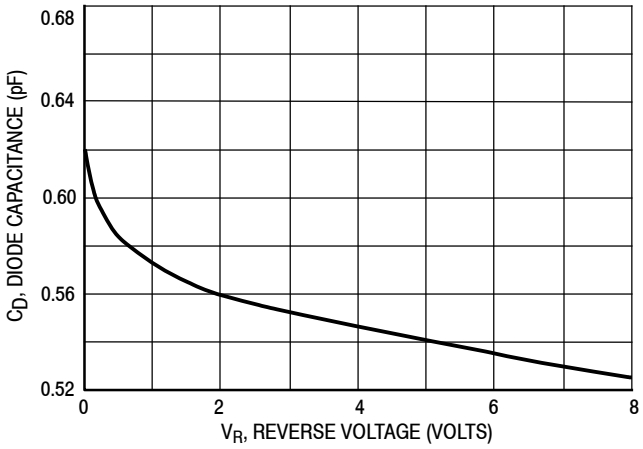


Figure 6. Capacitance

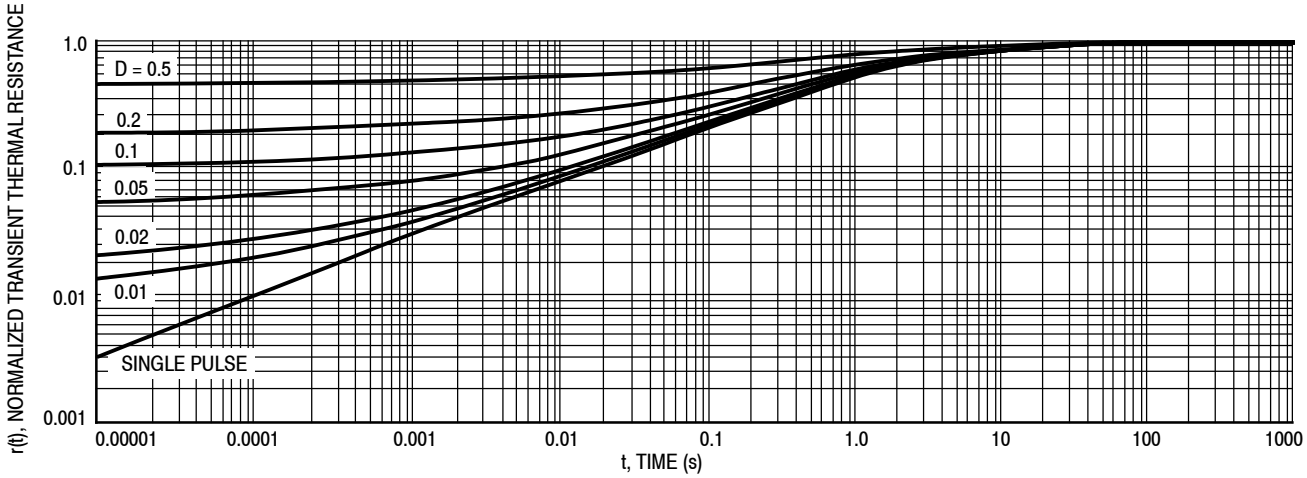


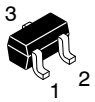
Figure 7. Normalized Thermal Response

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

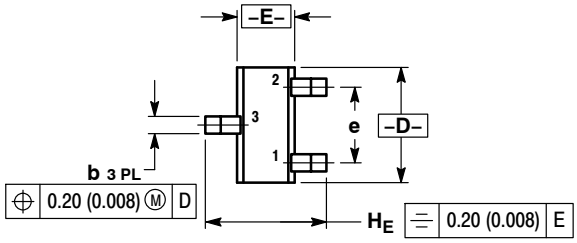
ON Semiconductor®

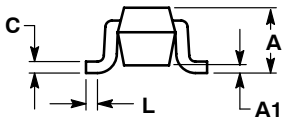
SC−75/SOT−416
CASE 463−01
ISSUE G

DATE 07 AUG 2015



SCALE 4:1





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H_E	1.50	1.60	1.70	0.060	0.063	0.067

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

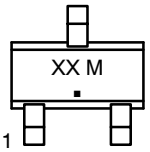
STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN

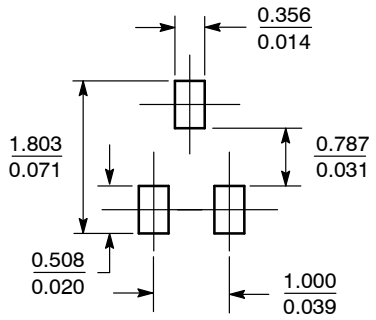
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**SC−75/SOT−416**	**PAGE 1 OF 1**

PUBLICATION ORDERING INFORMATION

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